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(54) Title: PRODUCTION METHOD OF A CAPACITOR

(57) Abstract: A method for producing a capacitor having a good capacitance appearance factor and a low ESR comprising, as one electrode (anode), an electric conductor having pores and having formed on the surface thereof a dielectric layer and, as the other electrode (cathode), a semiconductor layer formed on the electric conductor by energization in an electrolytic solution, the method comprising impregnating pores with a semiconductor layer-forming precursor before energization to render the concentration of semiconductor layer-forming precursor in pores higher than that of semiconductor layer-forming precursor in the electrolytic solution; a capacitor produced by the method; and an electronic circuit and an electronic device using the capacitor.

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